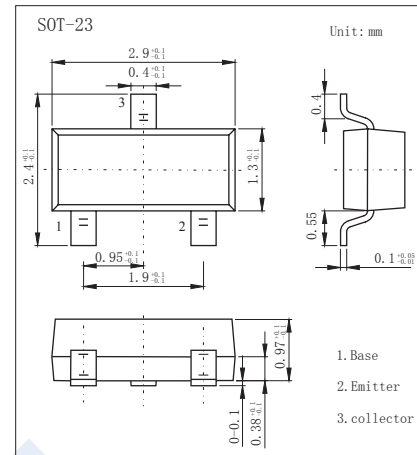


## PNP Transistors

### 2SA1330

#### ■ Features

- High DC current gain.
- High voltage.
- Complementary to 2SC3360



#### ■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V <sub>CB0</sub>	-200	V
Collector-emitter voltage	V <sub>CEO</sub>	-200	V
Emitter-base voltage	V <sub>EBO</sub>	-5	V
Collector current	I <sub>c</sub>	-100	mA
Total power dissipation	P <sub>T</sub>	200	mW
Junction temperature	T <sub>j</sub>	150	°C
Storage temperature	T <sub>stg</sub>	-55 to +150	°C

#### ■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V <sub>CB0</sub>	I <sub>c</sub> = -100 μA, I <sub>E</sub> =0	-200			V
Collector- emitter breakdown voltage	V <sub>CEO</sub>	I <sub>c</sub> = -1 mA, I <sub>B</sub> =0	-200			
Emitter - base breakdown voltage	V <sub>EBO</sub>	I <sub>E</sub> = -100 μA, I <sub>c</sub> =0	-5			
Collector-base cut-off current	I <sub>CB0</sub>	V <sub>CB</sub> = -200 V, I <sub>E</sub> =0			-100	nA
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> = -5V, I <sub>c</sub> =0			-100	
Collector-emitter saturation voltage *	V <sub>CE(sat)</sub>	I <sub>c</sub> =-50 mA, I <sub>B</sub> =- 5mA		-0.21	-0.3	V
Base - emitter saturation voltage *	V <sub>BE(sat)</sub>	I <sub>c</sub> =-50 mA, I <sub>B</sub> =- 5mA		-0.8	-1.2	
Base - emitter voltage *	V <sub>BE</sub>	V <sub>CE</sub> = -10V, I <sub>c</sub> = -10mA	-0.6	-0.65	-0.7	
DC current gain *	h <sub>FE</sub> (1)	V <sub>CE</sub> = -10V, I <sub>c</sub> = -10mA	90	200	450	
	h <sub>FE</sub> (2)	V <sub>CE</sub> = -10V, I <sub>c</sub> =-50mA	50	195		
Turn-on time	t <sub>r</sub>	V <sub>CC</sub> =-10V, V <sub>BE(off)</sub> =2.5V I <sub>c</sub> =-10mA, I <sub>B1</sub> =I <sub>B2</sub> =-1.0mA		0.16		us
Storage time	t <sub>s</sub>			1.3		
Turn-off time	t <sub>off</sub>			0.18		
Collector output capacitance	C <sub>ob</sub>	V <sub>CB</sub> = -30V, I <sub>E</sub> = 0, f=1MHz		3.6		pF
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> = -10V, I <sub>E</sub> = 10mA		120		MHz

\* Pulse test: t<sub>p</sub> ≤ 350 us; duty cycle ≤ 0.02.

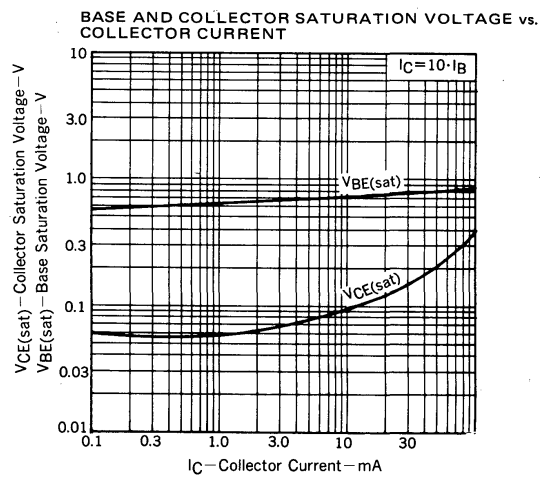
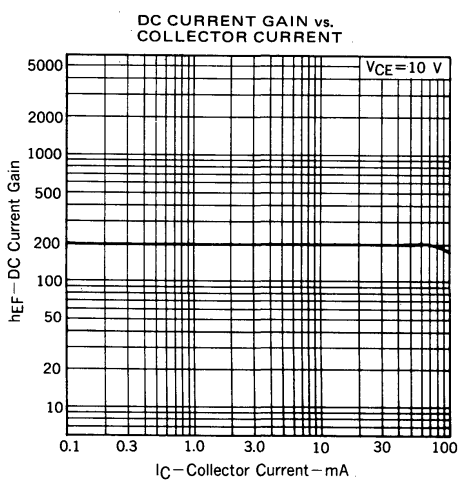
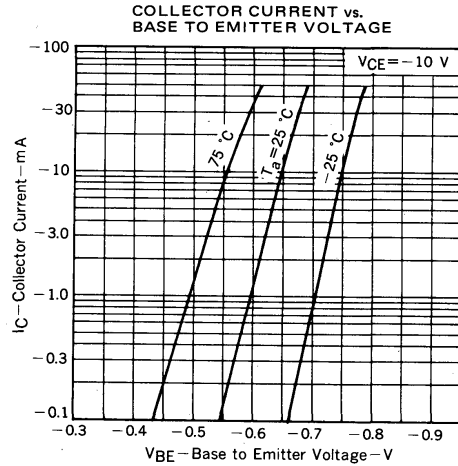
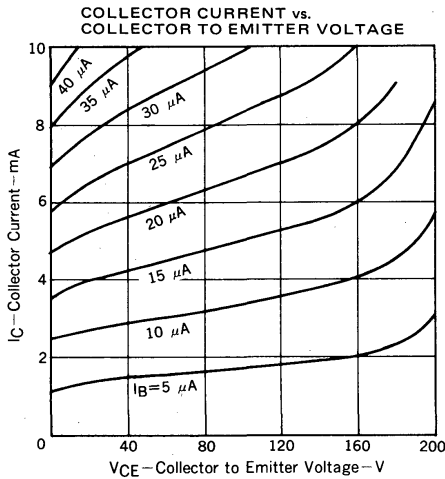
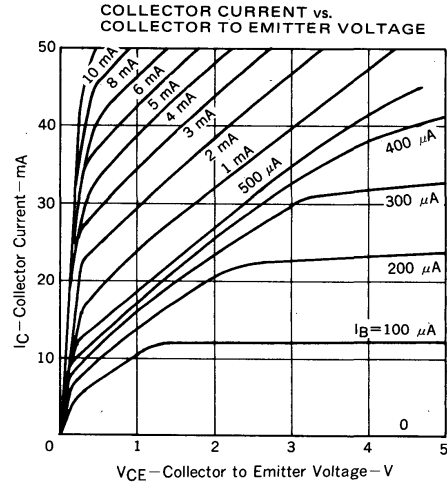
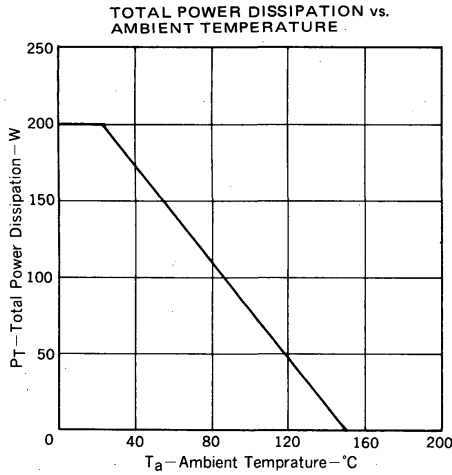
#### ■ Classification of h<sub>FE</sub>(1)

Type	2SA1330-O5	2SA1330-O6	2SA1330-O7
Range	90-180	135-270	200-450
Marking	O5	O6	O7

# PNP Transistors

## 2SA1330

### ■ Typical Characteristics



# PNP Transistors

## 2SA1330

### ■ Typical Characteristics

